

## N-channel 600 V, 0.085 $\Omega$ typ., 34 A MDmesh™ DM2 Power MOSFET in a D<sup>2</sup>PAK package

Datasheet - production data

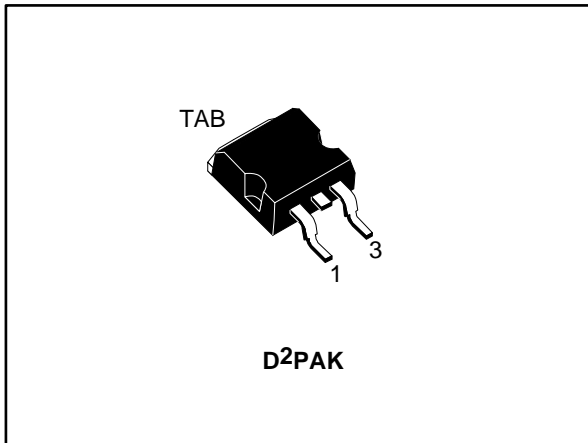
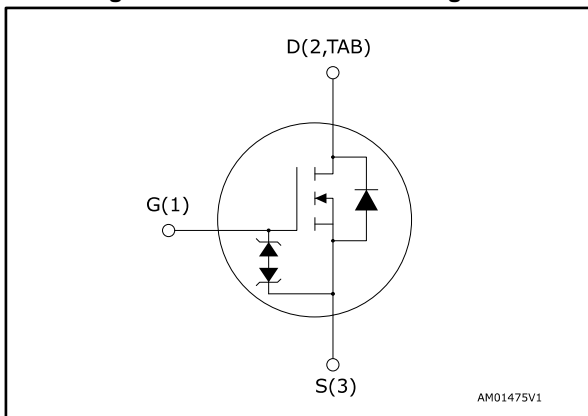


Figure 1: Internal schematic diagram



### Features

Order code	V <sub>DS</sub> @ T <sub>Jmax.</sub>	R <sub>DS(on)</sub> max.	I <sub>D</sub>	P <sub>TOT</sub>
STB43N60DM2	650 V	0.093 $\Omega$	34 A	250 W

- Fast-recovery body diode
- Extremely low gate charge and input capacitance
- Low on-resistance
- 100% avalanche tested
- Extremely high dv/dt ruggedness
- Zener-protected

### Applications

- Switching applications

### Description

This high voltage N-channel Power MOSFET is part of the MDmesh™ DM2 fast recovery diode series. It offers very low recovery charge ( $Q_{rr}$ ) and time ( $t_{rr}$ ) combined with low  $R_{DS(on)}$ , rendering it suitable for the most demanding high efficiency converters and ideal for bridge topologies and ZVS phase-shift converters.

Table 1: Device summary

Order code	Marking	Package	Packing
STB43N60DM2	43N60DM2	D <sup>2</sup> PAK	Tape and reel

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# 1 Electrical ratings

**Table 2: Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{GS}$	Gate-source voltage	$\pm 25$	V
$I_D$	Drain current (continuous) at $T_{case} = 25\text{ °C}$	34	A
	Drain current (continuous) at $T_{case} = 100\text{ °C}$	21	
$I_{DM}^{(1)}$	Drain current (pulsed)	136	A
$P_{TOT}$	Total dissipation at $T_{case} = 25\text{ °C}$	250	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	50	V/ns
$dv/dt^{(3)}$	MOSFET $dv/dt$ ruggedness	50	
$T_{stg}$	Storage temperature	-55 to 150	°C
$T_j$	Operating junction temperature		

**Notes:**

(1) Pulse width is limited by safe operating area.

(2)  $I_{SD} \leq 34\text{ A}$ ,  $di/dt=900\text{ A}/\mu\text{s}$ ;  $V_{DS\text{ peak}} < V_{(BR)DSS}$ ,  $V_{DD} = 400\text{ V}$ .

(3)  $V_{DS} \leq 480\text{ V}$ .

**Table 3: Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	0.50	°C/W
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	30	

**Notes:**

(1) When mounted on a 1-inch<sup>2</sup> FR-4, 2 Oz copper board.

**Table 4: Avalanche characteristics**

Symbol	Parameter	Value	Unit
$I_{AR}$	Avalanche current, repetitive or not repetitive	6	A
$E_{AS}^{(1)}$	Single pulse avalanche energy	800	mJ

**Notes:**

(1) starting  $T_j = 25\text{ °C}$ ,  $I_D = I_{AR}$ ,  $V_{DD} = 50\text{ V}$ .

## 2 Electrical characteristics

( $T_{\text{case}} = 25\text{ °C}$  unless otherwise specified)

**Table 5: Static**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$ , $I_D = 1\text{ mA}$	600			V
$I_{DSS}$	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$ , $V_{DS} = 600\text{ V}$			1	$\mu\text{A}$
		$V_{GS} = 0\text{ V}$ , $V_{DS} = 600\text{ V}$ , $T_{\text{case}} = 125\text{ °C}$			100	
$I_{GSS}$	Gate-body leakage current	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 25\text{ V}$			$\pm 5$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$ , $I_D = 17\text{ A}$		0.085	0.093	$\Omega$

**Table 6: Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{ISS}$	Input capacitance	$V_{DS} = 100\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0\text{ V}$	-	2500	-	$\text{pF}$
$C_{OSS}$	Output capacitance		-	120	-	
$C_{RSS}$	Reverse transfer capacitance		-	3	-	
$C_{OSS\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{DS} = 0\text{ to }480\text{ V}$ , $V_{GS} = 0\text{ V}$	-	200	-	$\text{pF}$
$R_G$	Intrinsic gate resistance	$f = 1\text{ MHz}$ , $I_D = 0\text{ A}$	-	4	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 480\text{ V}$ , $I_D = 34\text{ A}$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 15: "Gate charge test circuit"</a> )	-	56	-	$\text{nC}$
$Q_{gs}$	Gate-source charge		-	13	-	
$Q_{gd}$	Gate-drain charge		-	30	-	

**Notes:**

<sup>(1)</sup>  $C_{OSS\text{ eq.}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{OSS}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$ .

**Table 7: Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}$ , $I_D = 25\text{ A}$ $R_G = 4.7\text{ }\Omega$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 14: "Switching times test circuit for resistive load"</a> and <a href="#">Figure 19: "Switching time waveform"</a> )	-	29	-	$\text{ns}$
$t_r$	Rise time		-	27	-	
$t_{d(off)}$	Turn-off delay time		-	85	-	
$t_f$	Fall time		-	6	-	

Table 8: Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		34	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		136	A
$V_{SD}^{(2)}$	Forward on voltage	$V_{GS} = 0\text{ V}$ , $I_{SD} = 34\text{ A}$	-		1.6	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 34\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 60\text{ V}$ (see <a href="#">Figure 16: "Test circuit for inductive load switching and diode recovery times"</a> )	-	120		ns
$Q_{rr}$	Reverse recovery charge		-	0.6		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	10.4		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 34\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 60\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$ (see <a href="#">Figure 16: "Test circuit for inductive load switching and diode recovery times"</a> )	-	240		ns
$Q_{rr}$	Reverse recovery charge		-	2.4		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	20.5		A

**Notes:**

- (1) Pulse width is limited by safe operating area.  
(2) Pulse test: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%.

## 2.1 Electrical characteristics (curves)

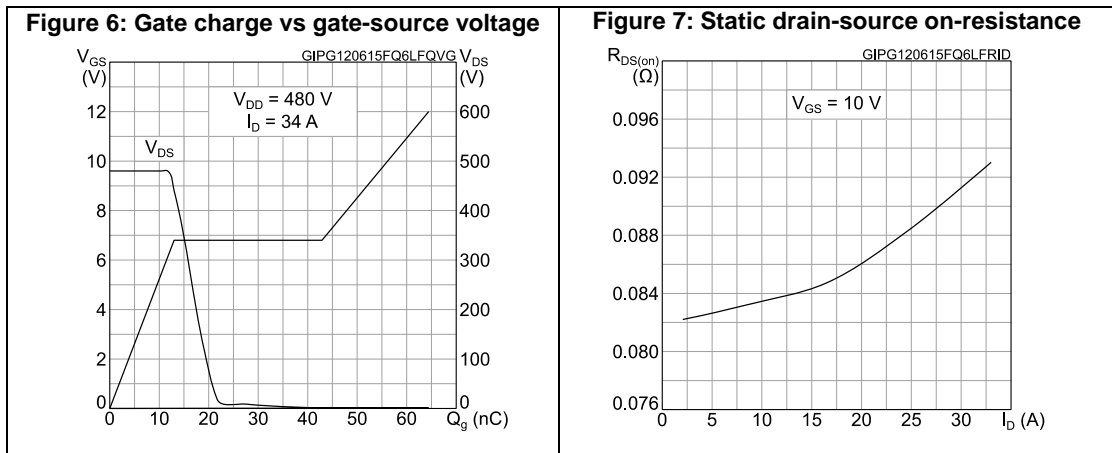
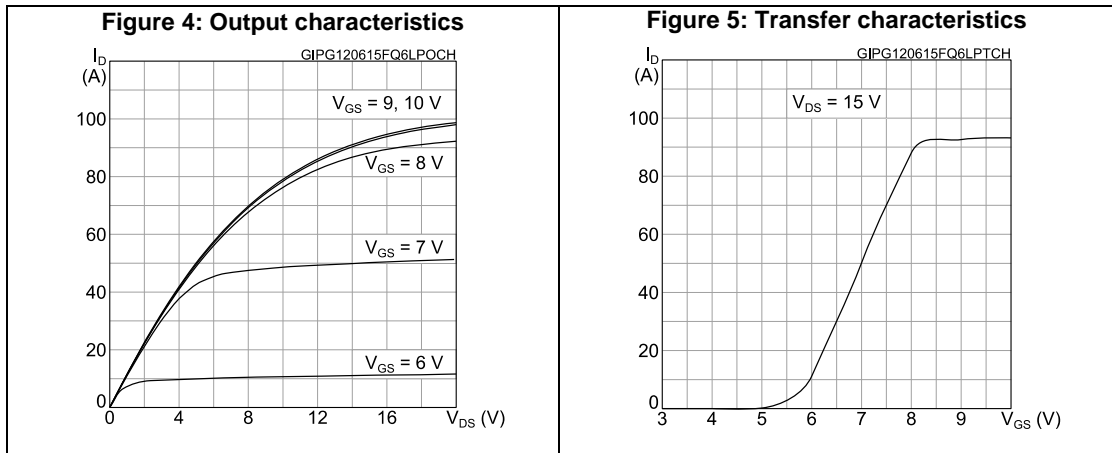
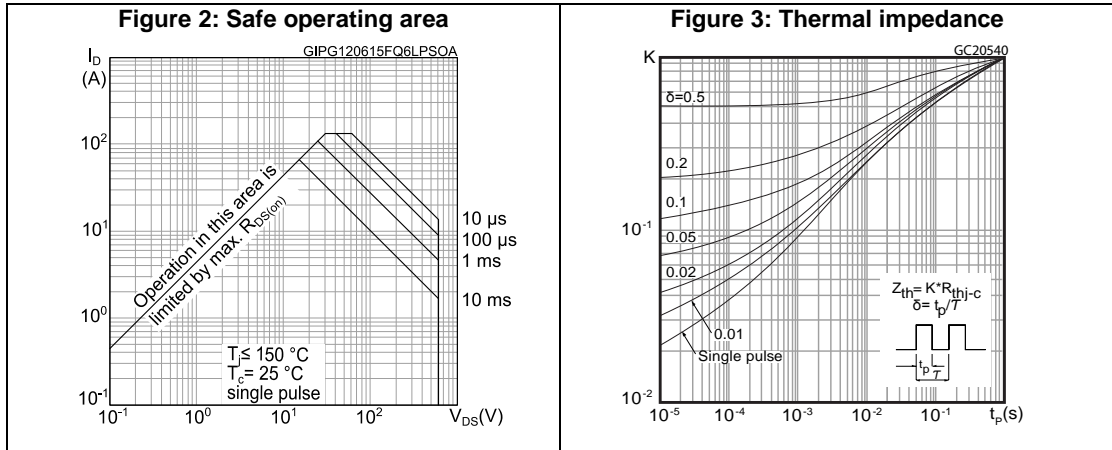


Figure 8: Capacitance variations

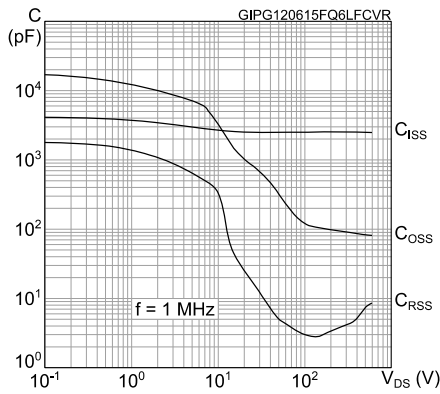


Figure 9: Normalized gate threshold voltage vs temperature

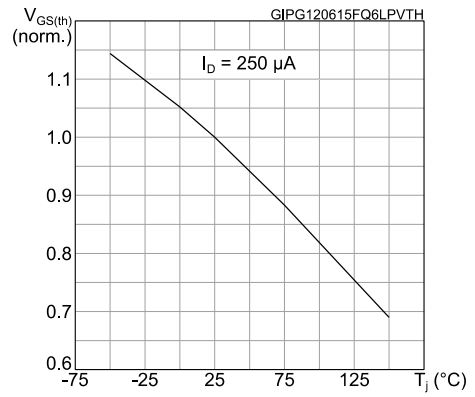


Figure 10: Normalized on-resistance vs temperature

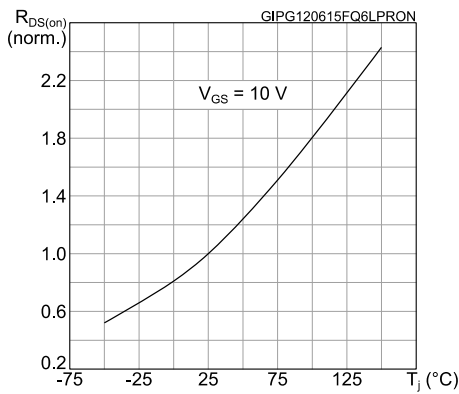


Figure 11: Normalized V(BR)DSS vs temperature

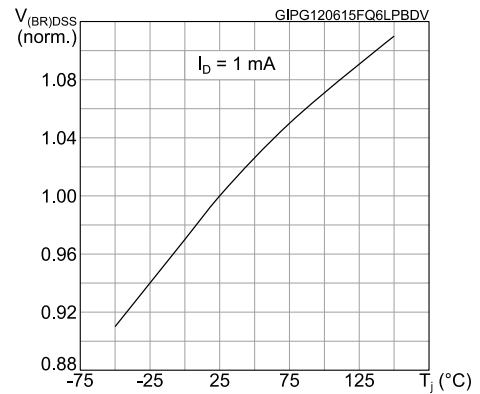


Figure 12: Output capacitance stored energy

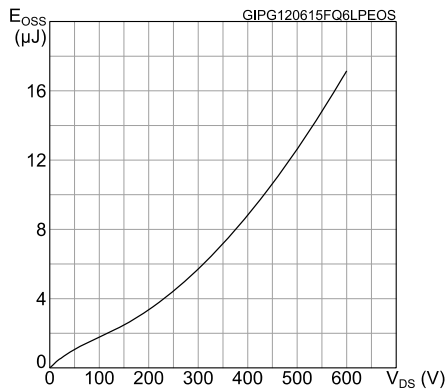
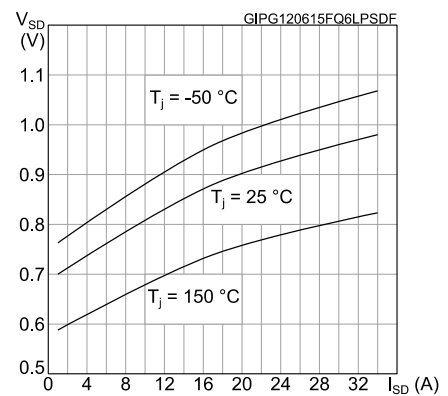
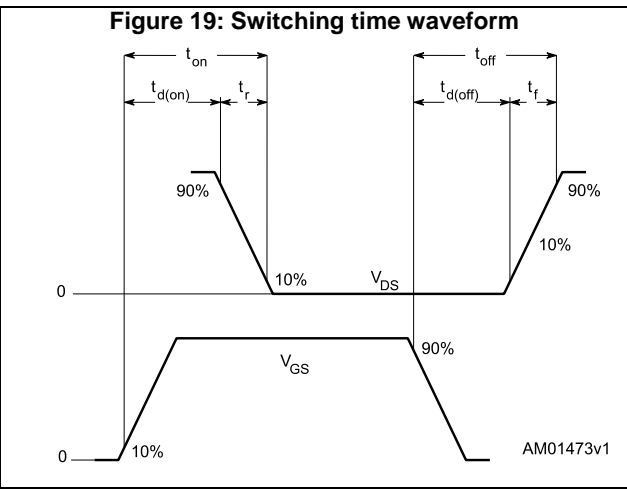
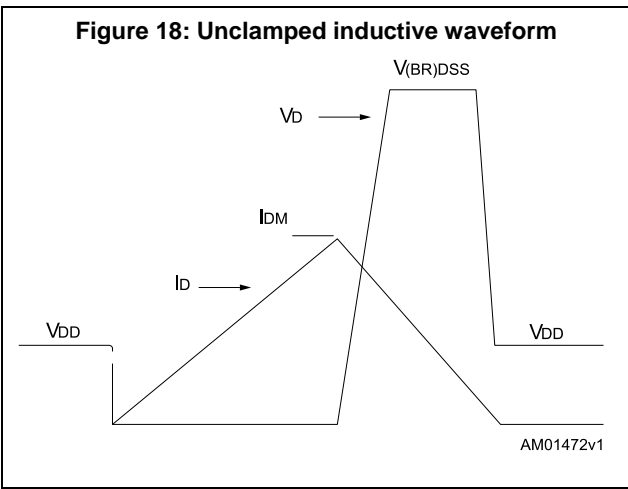
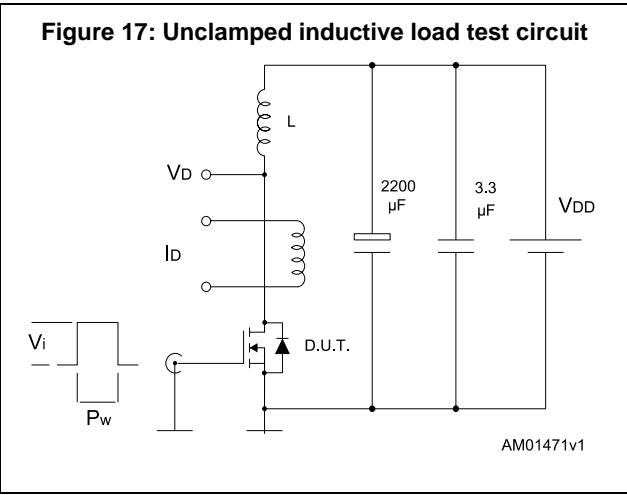
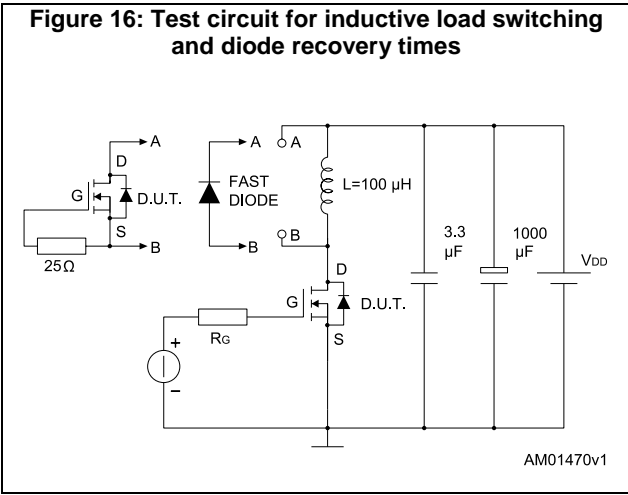
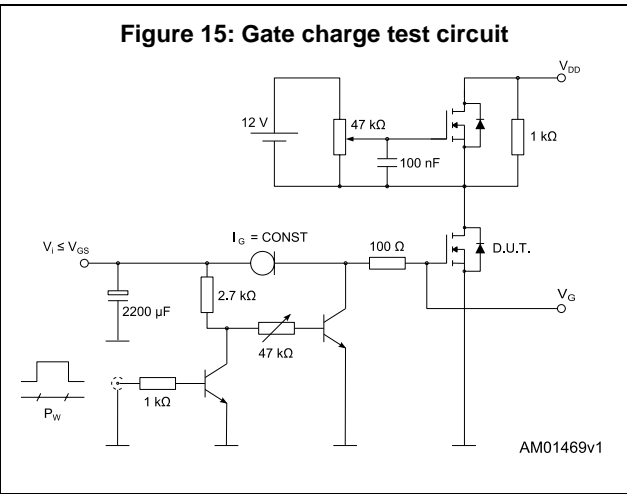
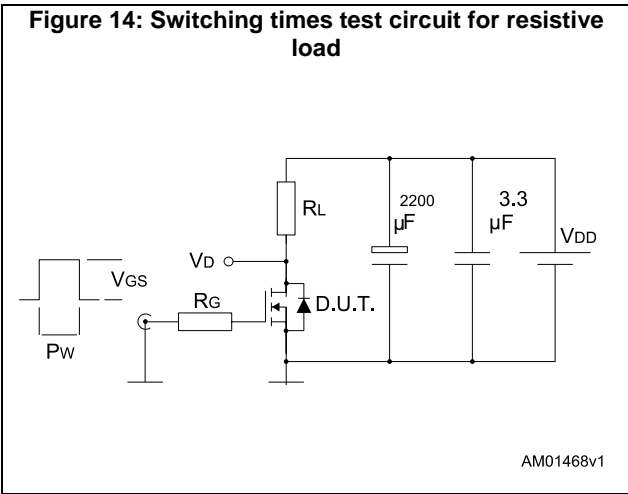


Figure 13: Source-drain diode forward characteristics



### 3 Test circuits





## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

### 4.1 D<sup>2</sup>PAK (TO-263) type A package information

Figure 20: D<sup>2</sup>PAK (TO-263) type A package outline

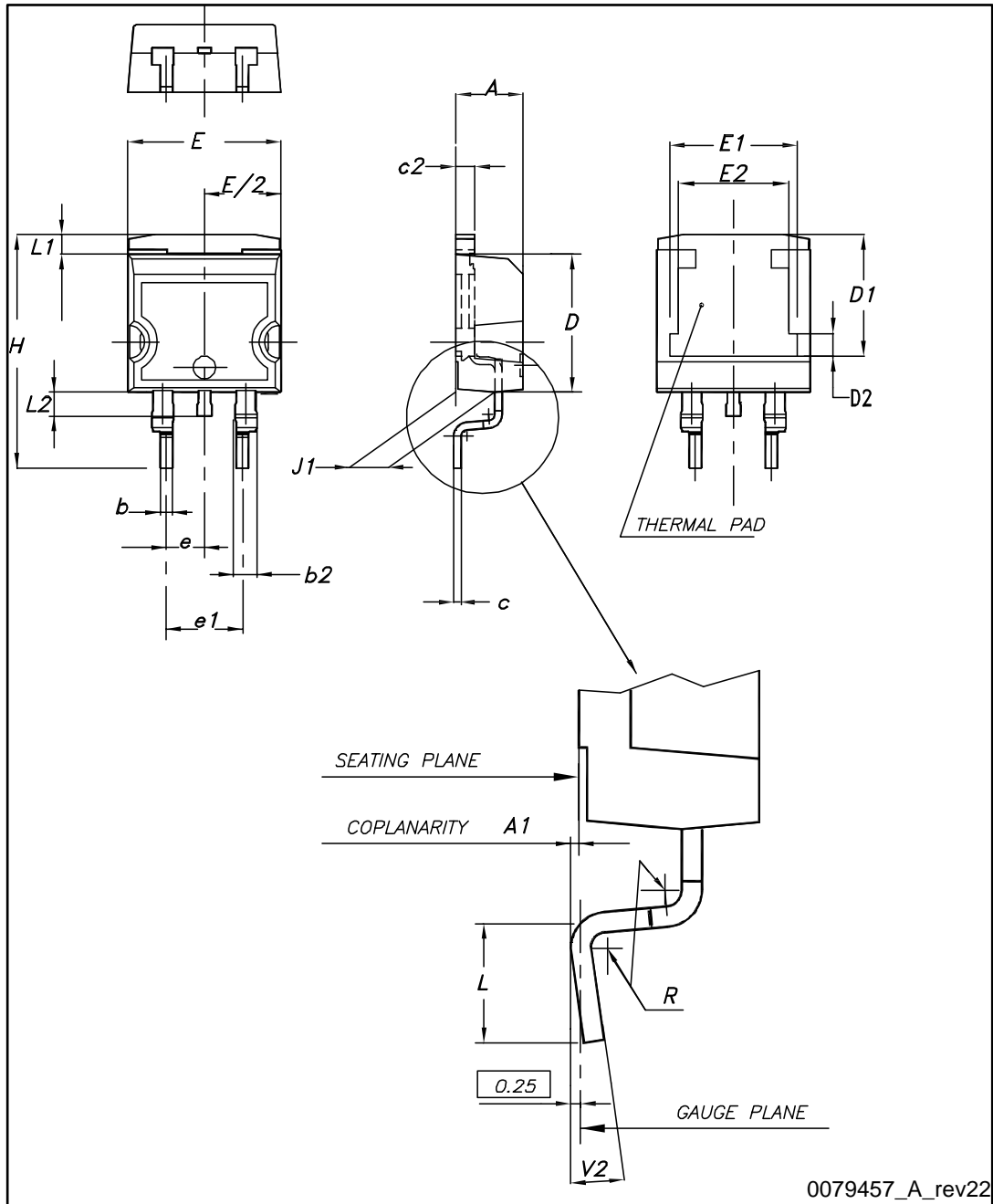
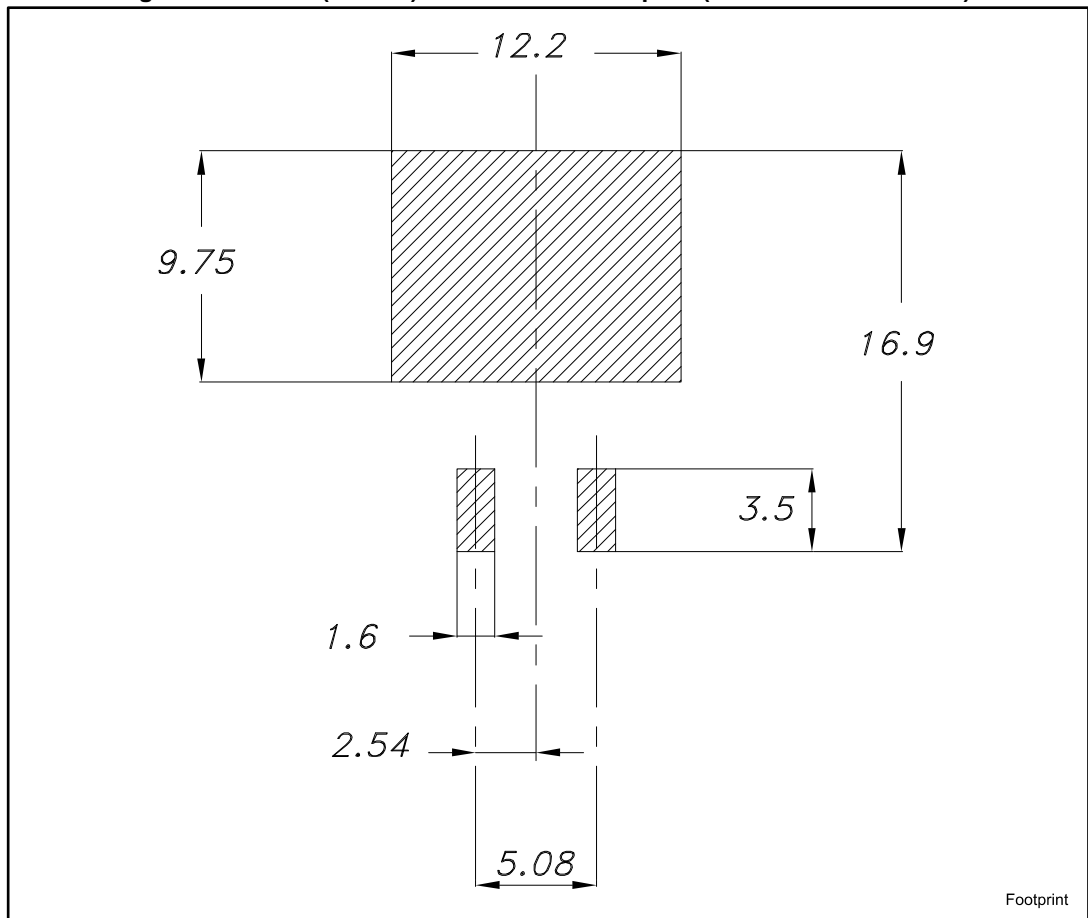


Table 9: D<sup>2</sup>PAK (TO-263) type A package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50	7.75	8.00
D2	1.10	1.30	1.50
E	10		10.40
E1	8.50	8.70	8.90
E2	6.85	7.05	7.25
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 21: D<sup>2</sup>PAK (TO-263) recommended footprint (dimensions are in mm)



## 4.2 D<sup>2</sup>PAK packing information

Figure 22: Tape

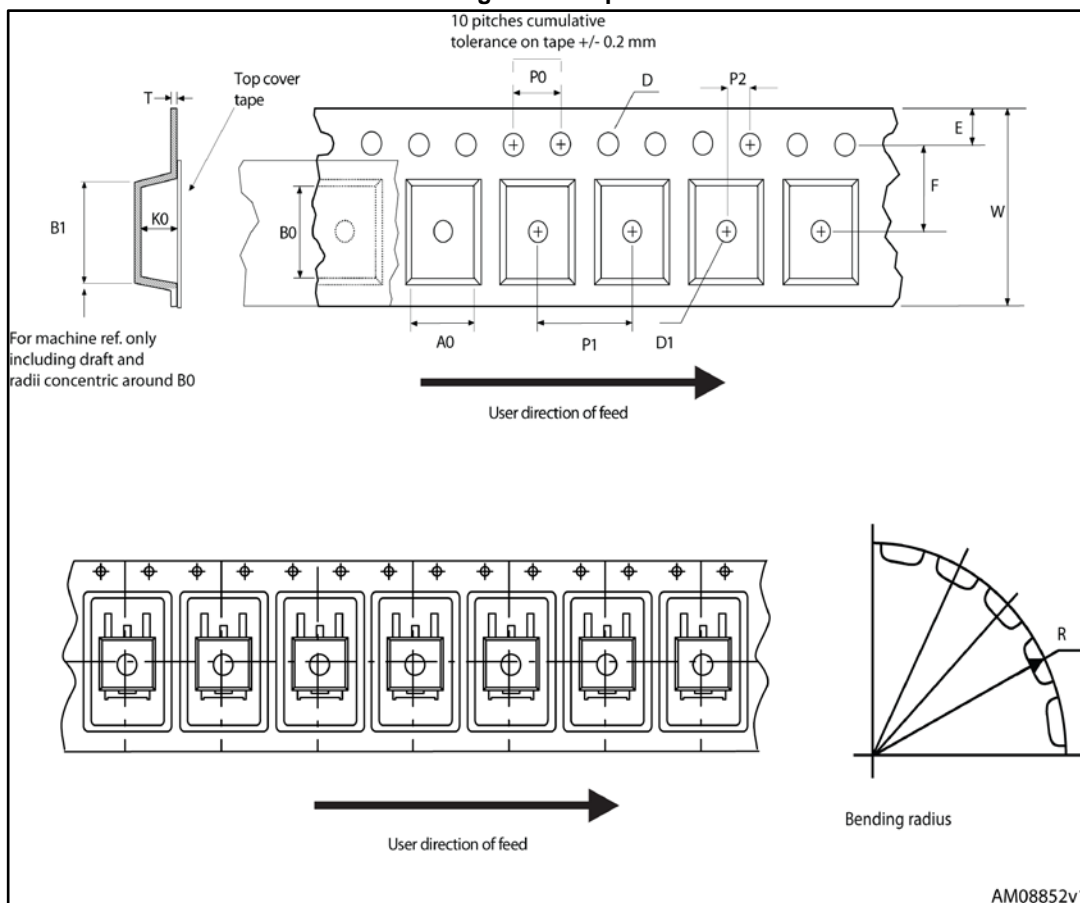
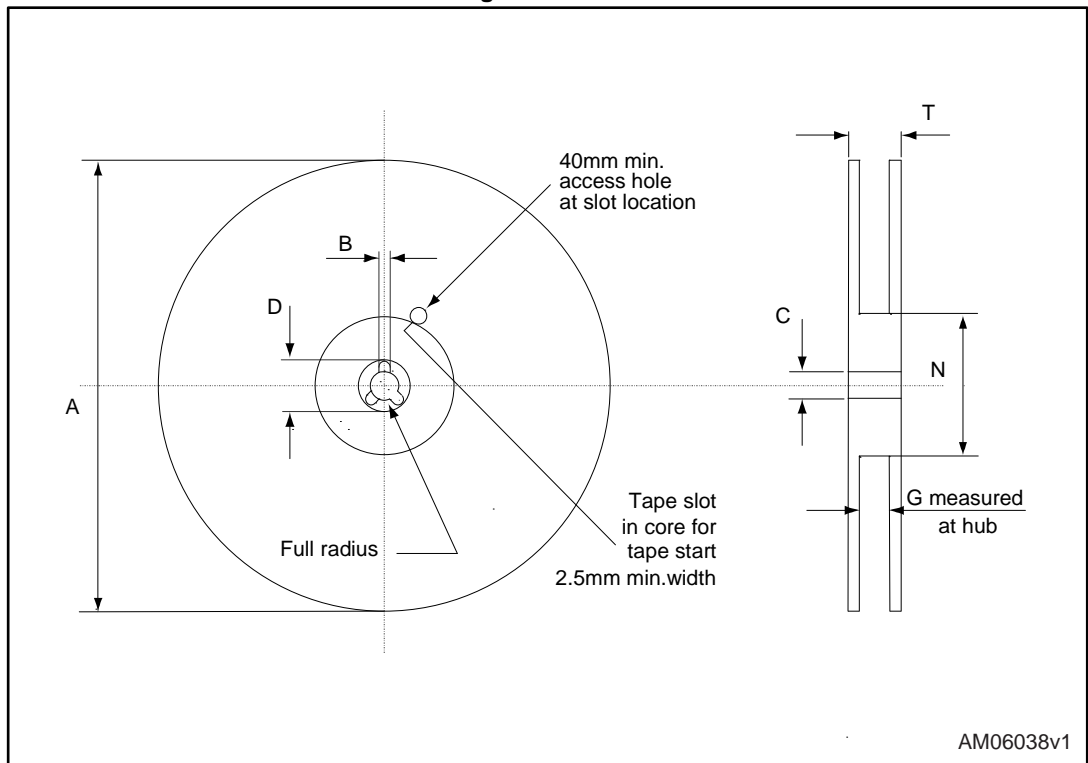


Figure 23: Reel



AM06038v1

Table 10: D<sup>2</sup>PAK tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base qty		1000
P2	1.9	2.1	Bulk qty		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

## 5 Revision history

Table 11: Document revision history

Date	Revision	Changes
02-Jul-2015	1	Initial release.

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